

FIG.1

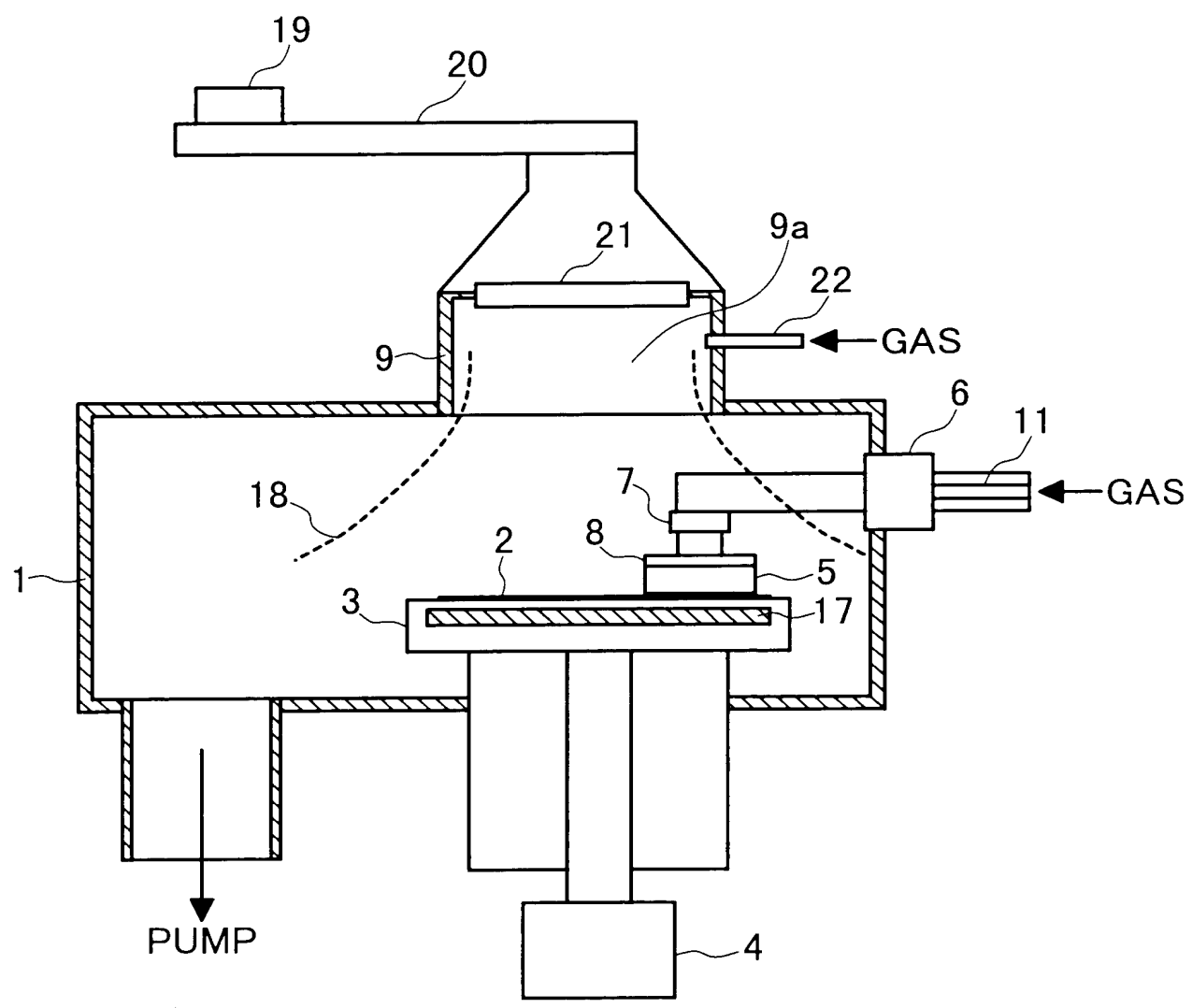


FIG.2

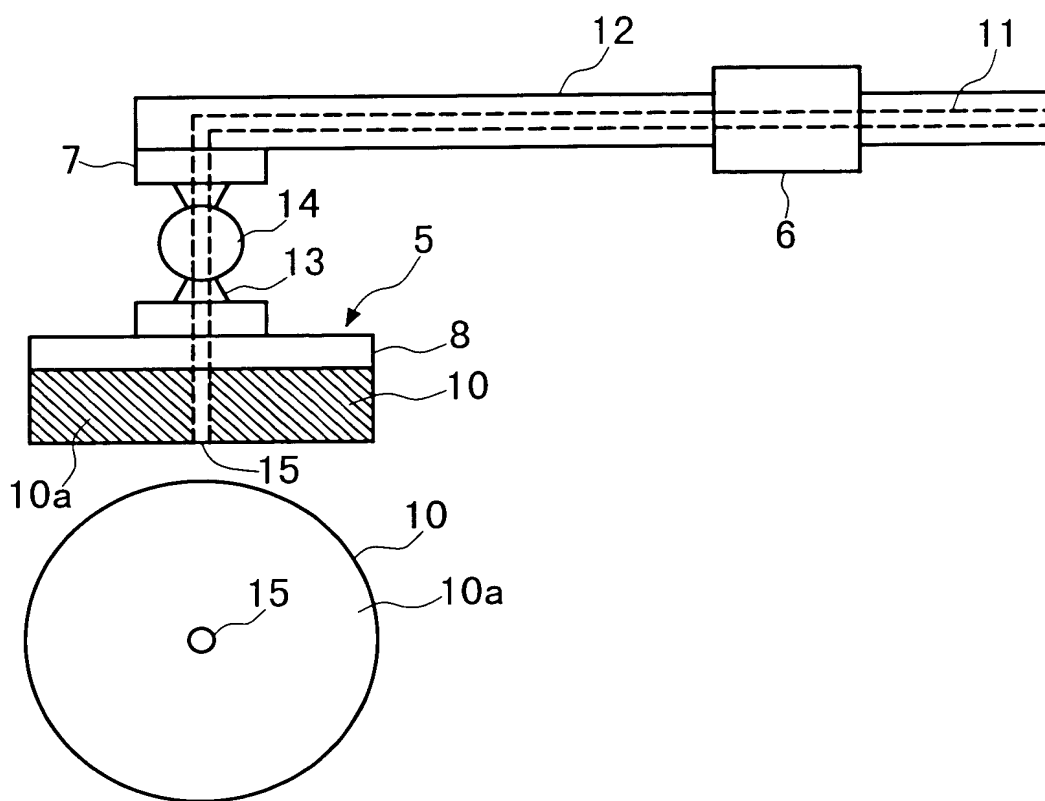


FIG.3

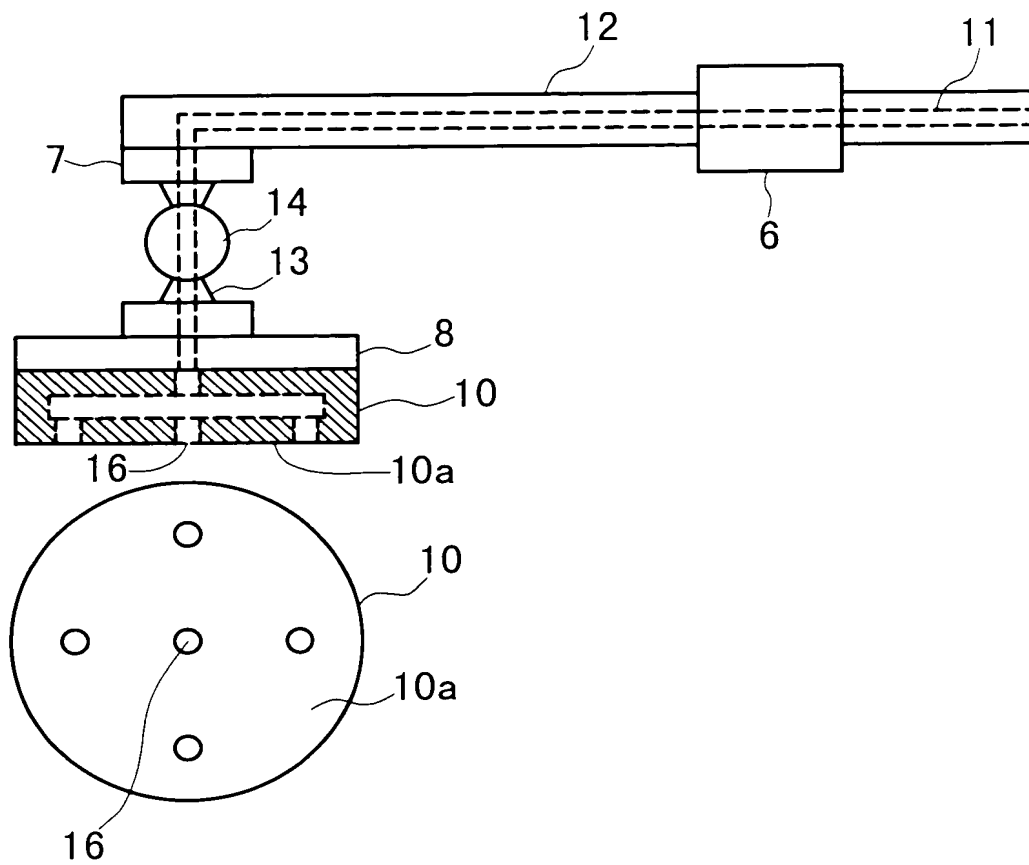


FIG.4

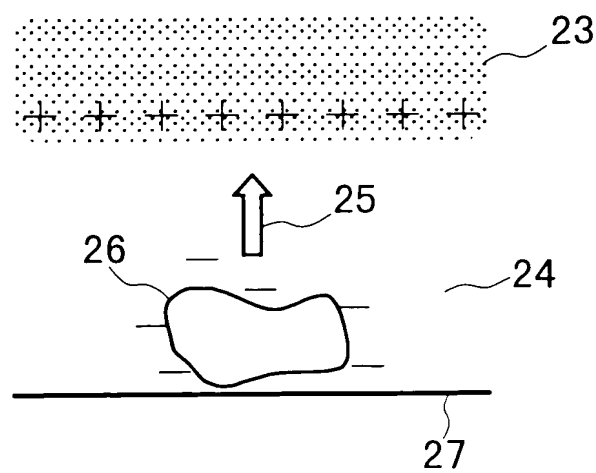


FIG.5

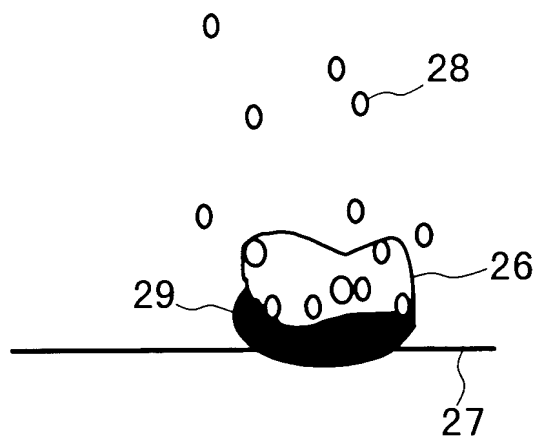


FIG.6

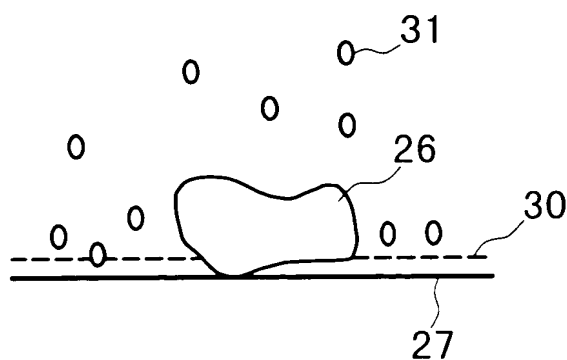


FIG.7

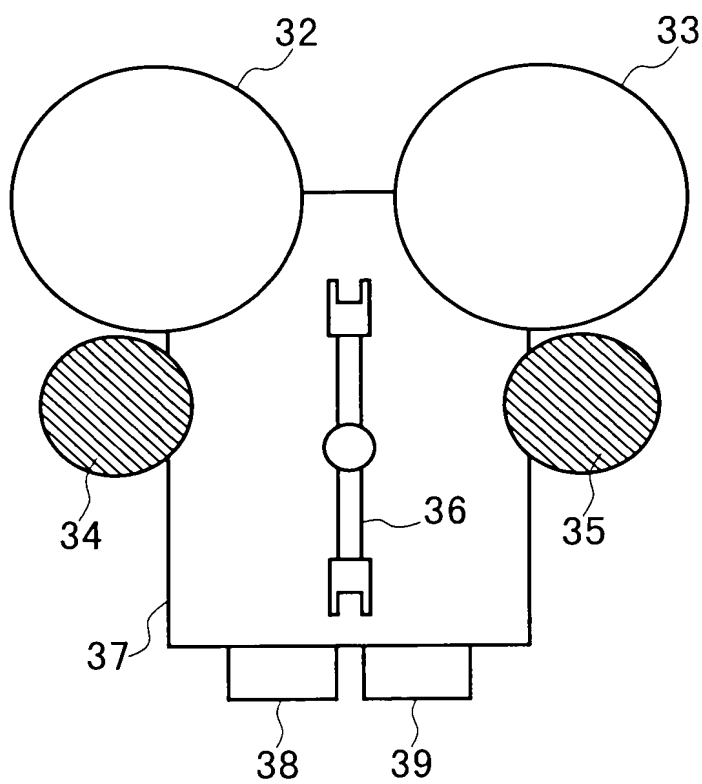


FIG.8

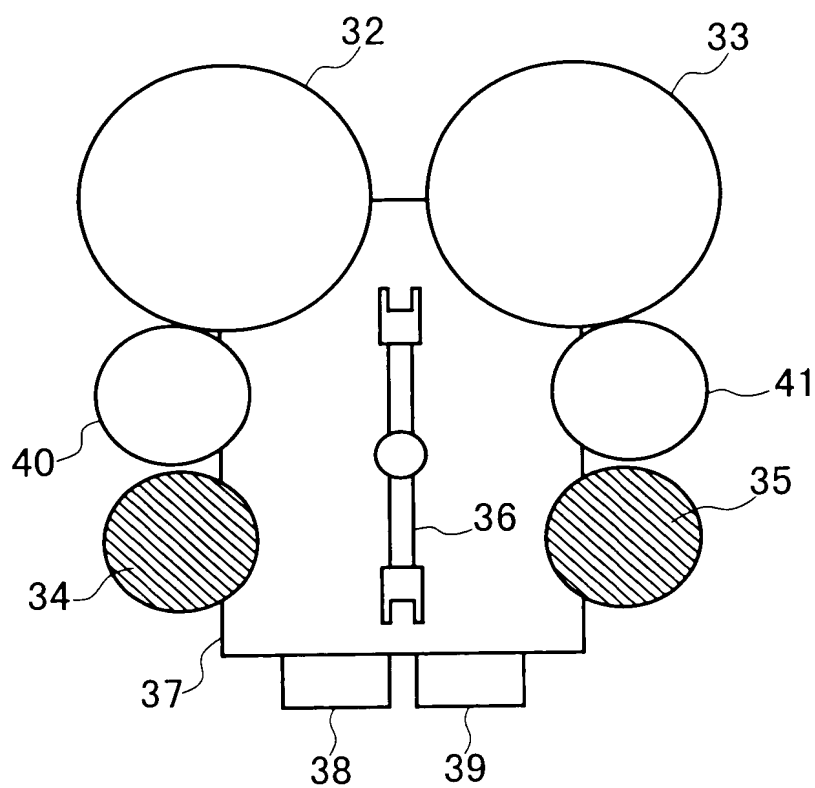


FIG.9

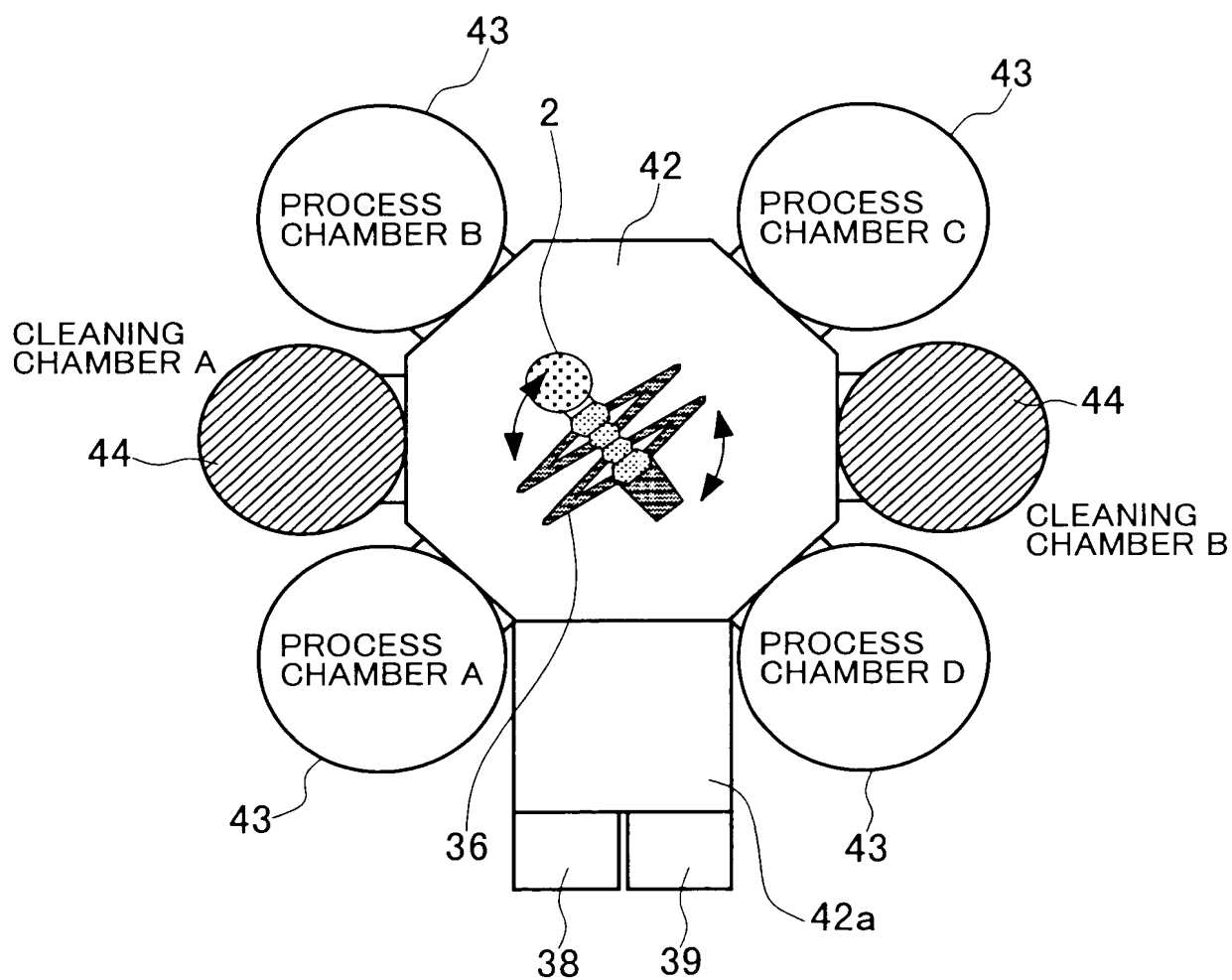


FIG.10A

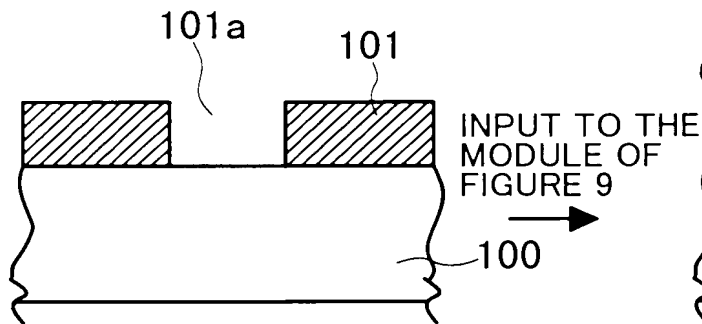


FIG.10B

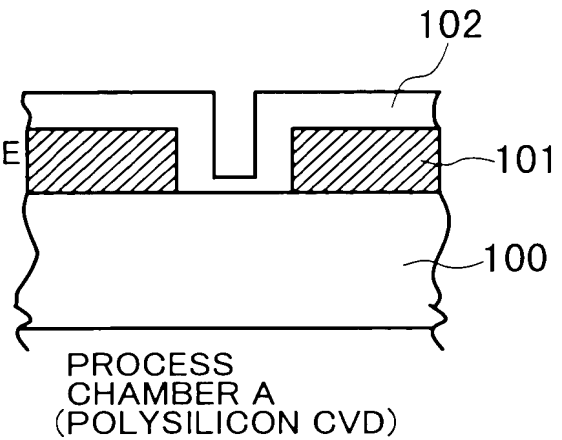


FIG.10C (CLEANING CHAMBER A)

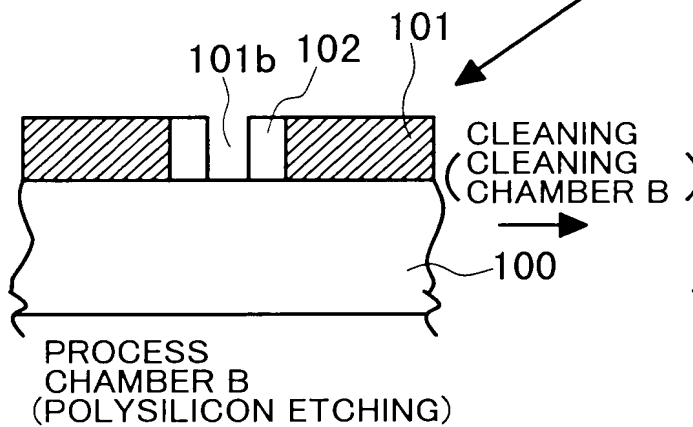


FIG.10D

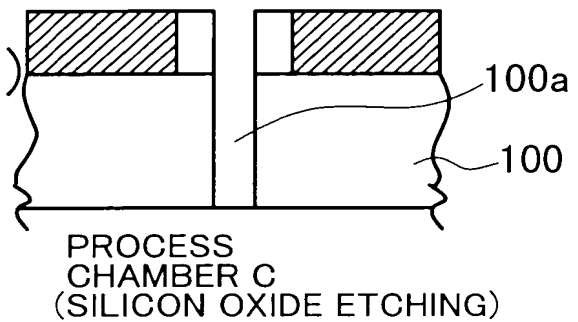


FIG.10E

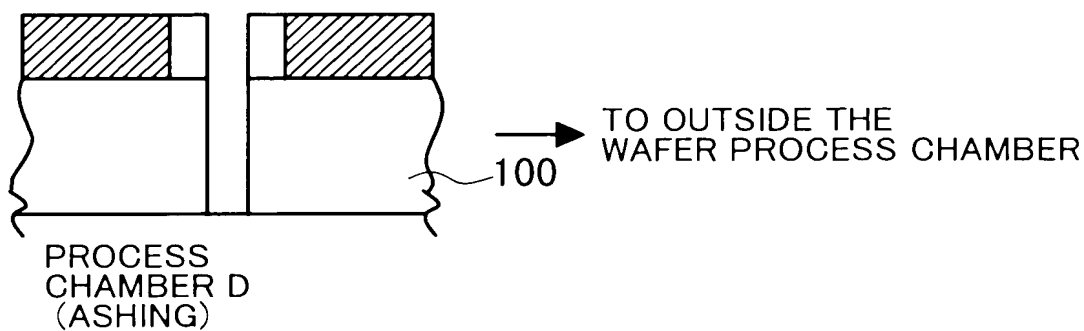


FIG.11A

FABRICATION
OF DEVICE ISOLATION
REGION AND DEPOSITION
OF POLYSILICON

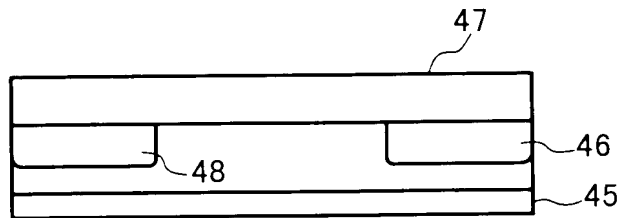


FIG.11B

FABRICATION
OF GATE ELECTRODE
(POLYSILICON ETCHING)

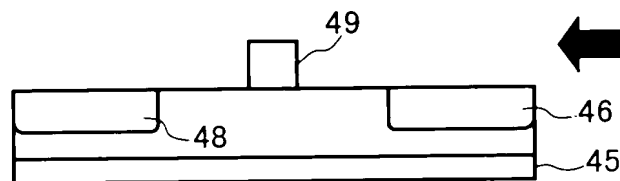


FIG.11C

FABRICATION
OF EXTENSION

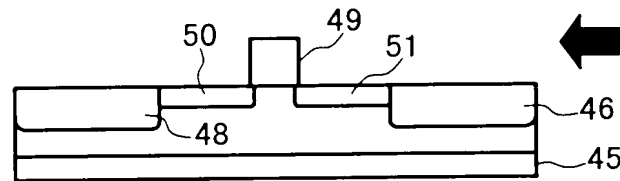


FIG.11D

DEPOSITION
OF NITRIDE FILM

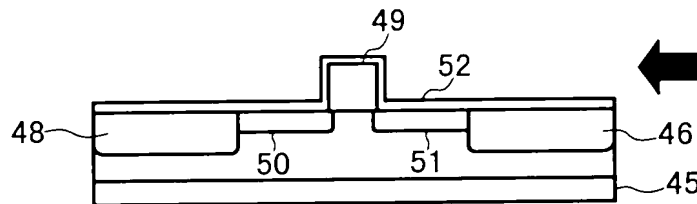


FIG.11E

FABRICATION
OF GATE SIDE
WALL FILM

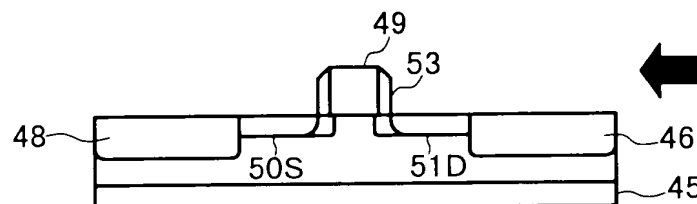


FIG.11F

FABRICATION
OF SILISIDE

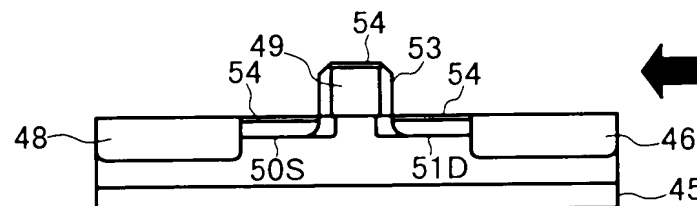


FIG.12A

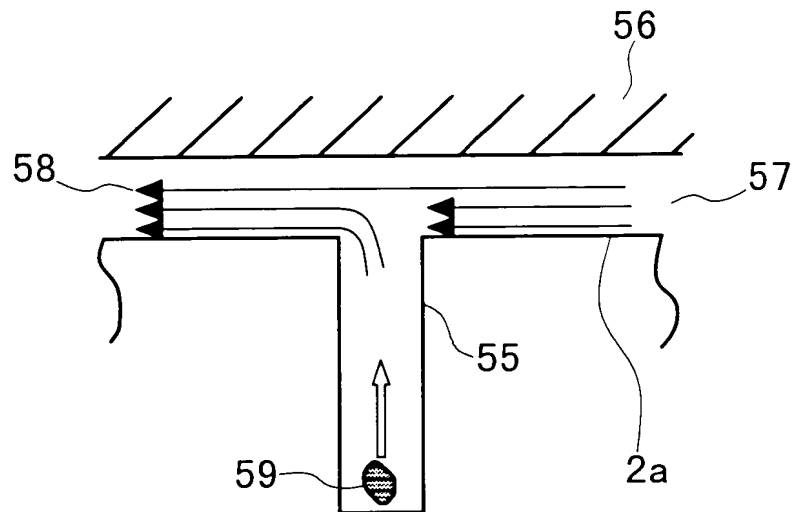
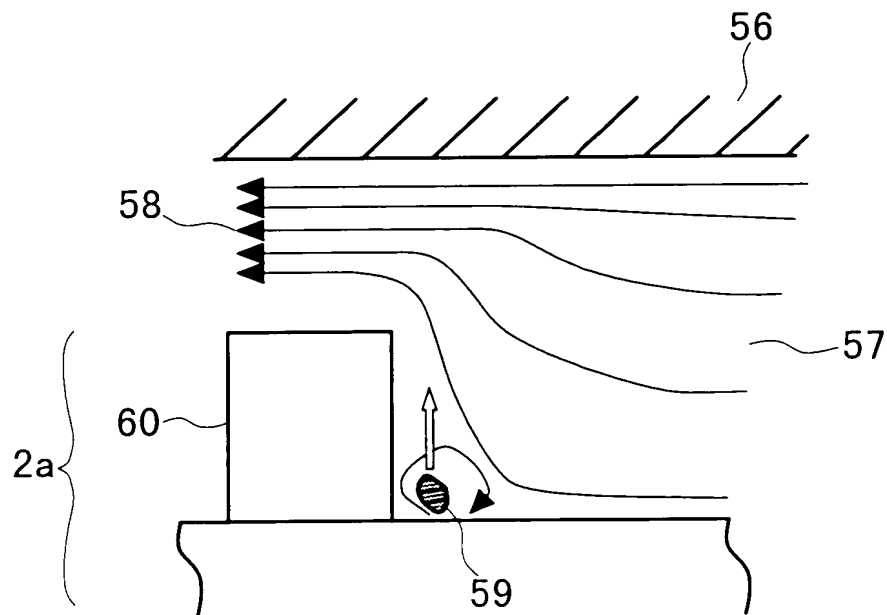


FIG.12B



A cross-sectional schematic diagram of a wafer processing apparatus. The diagram shows a wafer (2) with a wafer surface. Above the wafer is a chamber (5) containing a central vertical tube (10) and two side chambers (8). The central tube is labeled 'Ar' and has an arrow pointing downwards. The side chambers are labeled 'FINE MOVING SYSTEM'. The top of the chamber is labeled 'ROUGH MOVING SYSTEM'. A 'HIGH SPEED GAS FLOW' is indicated by arrows pointing from the right side of the chamber towards the wafer surface. A dashed circle is shown on the wafer surface, and a large arrow points downwards from the center of the diagram.

